June 14, 2012

RFMD® Announces Availability of Design Kits for Agilent Technologies' Advanced Design System 2011 Software

GREENSBORO, N.C., June 14, 2012 (GLOBE NEWSWIRE) -- RF Micro Devices, Inc. (Nasdaq:RFMD), a global leader in the design and manufacture of high-performance radio frequency components and compound semiconductor technologies, announced today that its Foundry Services business unit has updated its process design kits (PDKs) for use with Agilent Technologies' recently released Advanced Design System (ADS) 2011 EDA software. The enhanced PDKs are available immediately to current and prospective RFMD Foundry Services customers for RFMD's Gallium Nitride (GaN) and Gallium Arsenide (GaAs) process technologies.

The RFMD PDKs support a complete ADS front- to back-end MMIC design flow with scalable devices, a native design rule checker, and the layout capabilities in ADS 2011. The PDKs work seamlessly with ADS 2011, ADS 2009 Update 1 and ADS 2008 Update 2, enabling RFMD Foundry Services customers to take full advantage of the significant performance advantages of ADS 2011.

RFMD's GaN and GaAs process technologies are available to Foundry Services customers, supported by RFMD's industry-leading cycle times. RFMD's foundry offerings include GaN1 (GaN for high power), a 0.5-micron GaN on SiC process technology enabling 65V CW operation and optimized for maximum performance at 4 GHz and below. RFMD's GaN1 power technology provides a high breakdown voltage above 400V, while RFMD's GaN2 is a 0.5-micron GaN on SiC process technology offering high linearity for high performance communications systems. Both GaN technologies are manufactured in RFMD's Greensboro, NC, fab, one of the world's largest III-V fabs.

The Greensboro fab also manufactures HBT8D, RFMD's high-volume rugged InGap technology for handset and mixed signal applications, and IPC3, an integrated passive component technology that complements RFMD's GaN technology portfolio with high power compatibility.

Additional RFMD foundry offerings include FD25, a low noise, 0.25-micron GaAs pHEMT technology, and FD30, a high power 0.3-micron GaAs pHEMT technology, both of which support applications up through 25 GHz. RFMD's technology portfolio also includes FET1H, a 0.6-micron GaAs pHEMT technology, and FET2D, a 0.6-micron GaAs E/D pHEMT technology. Each of RFMD's pHEMT technologies is manufactured in the Company's Newton Aycliffe, UK, fab.

Dr. Tom Joseph, manager of technology in RFMD's Foundry Services business unit, said, "The ADS 2011 release provides RFMD Foundry customers access to Agilent's latest multi-technology platform for our GaN and GaAs process technologies. By leveraging Agilent's new Library architecture and simulation enhancements, RFMD's foundry customers can improve their design efficiencies and reduce time-to-market for their end market products."

"We are very happy that our mutual customers can now leverage the ADS 2011 product enhancements in RFMD's GaN and GaAs technologies," said Juergen Hartung, foundry program manager of Agilent's EEs of EDA organization. "With these PDKs, our customers can now enjoy the industry's most comprehensive multi-technology design platform using Momentum, the industry-leading 3-D planar EM simulator, our integrated full 3-D FEM engine, the industry-proven design-for-manufacturing capabilities inside ADS, and an upgraded design rule checker. These capabilities are just some of the reasons the majority of MMIC designers choose ADS to increase performance, consistency and yield."

For more information on RFMD's Foundry Services go to www.rfmd.com/foundry or contact RFMDFoundryServices@rfmd.com.

About RFMD

RF Micro Devices, Inc. (Nasdaq:RFMD) is a global leader in the design and manufacture of high-performance radio frequency components and compound semiconductor technologies. RFMD's products enable worldwide mobility, provide enhanced connectivity and support advanced functionality in the mobile device, wireless infrastructure, wireless local area network (WLAN or WiFi), cable television (CATV)/broadband, Smart Energy/advanced metering infrastructure (AMI), and aerospace and defense markets. RFMD is recognized for its diverse portfolio of semiconductor technologies and RF systems expertise and is a preferred supplier to the world's leading mobile device, customer premises and communications equipment providers.

Headquartered in Greensboro, N.C., RFMD is an ISO 9001-, ISO 14001-, and ISO/TS 16949-certified manufacturer with worldwide engineering, design, sales and service facilities. RFMD is traded on the NASDAQ Global Select Market under the

symbol RFMD. For more information, please visit RFMD's web site at www.rfmd.com.

The RF Micro Devices, Inc. logo is available at http://www.globenewswire.com/newsroom/prs/?pkgid=6436

This press release includes "forward-looking statements" within the meaning of the safe harbor provisions of the Private Securities Litigation Reform Act of 1995. These forward-looking statements include, but are not limited to, statements about our plans, objectives, representations and contentions and are not historical facts and typically are identified by use of terms such as "may," "will," "should," "could," "expect," "plan," "anticipate," "believe," "estimate," "predict," "potential," "continue" and similar words, although some forward-looking statements are expressed differently. You should be aware that the forward-looking statements included herein represent management's current judgment and expectations, but our actual results, events and performance could differ materially from those expressed or implied by forward-looking statements. We do not intend to update any of these forward-looking statements or publicly announce the results of any revisions to these forward-looking statements, other than as is required under the federal securities laws. RF Micro Devices' business is subject to numerous risks and uncertainties, including variability in operating results, risks associated with the impact of global macroeconomic and credit conditions on our business and the business of our suppliers and customers, our reliance on a few large customers for a substantial portion of our revenue, the rate of growth and development of wireless markets, our ability to bring new products to market, our reliance on inclusion in third party reference designs for a portion of our revenue, our ability to manage channel partner and customer relationships, risks associated with the operation of our wafer fabrication, molecular beam epitaxy, assembly and test and tape and reel facilities, our ability to complete acquisitions and integrate acquired companies, including the risk that we may not realize expected synergies from our business combinations, our ability to attract and retain skilled personnel and develop leaders, variability in production yields, raw material costs and availability, our ability to reduce costs and improve margins in response to declining average selling prices, our ability to adjust production capacity in a timely fashion in response to changes in demand for our products, dependence on gallium arsenide (GaAs) for the majority of our products, dependence on third parties, and substantial reliance on international sales and operations. These and other risks and uncertainties, which are described in more detail in RF Micro Devices' most recent Annual Report on Form 10-K and other reports and statements filed with the Securities and Exchange Commission, could cause actual results and developments to be materially different from those expressed or implied by any of these forward-looking statements.

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Source: RF Micro Devices